

isc P-Channel MOSFET Transistor

IRF9540N,IIRF9540N

• FEATURES

- Static drain-source on-resistance:
 $R_{DS(on)} \leq 0.117 \Omega$
- Enhancement mode:
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• DESCRIPTION

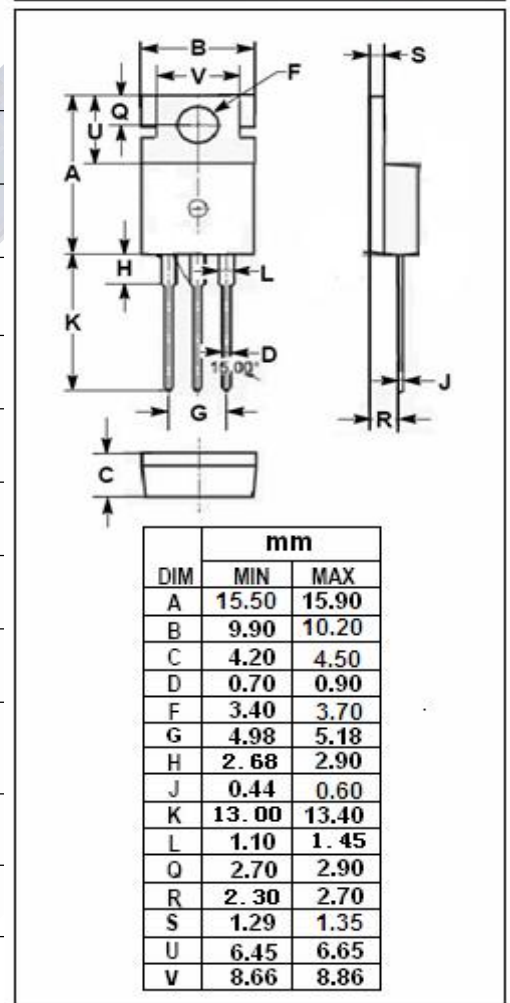
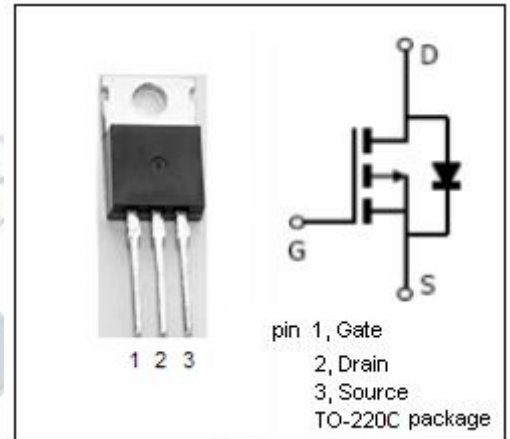
- Combine with the fast switching speed and ruggedized device design, provide the designer with an extremely efficient and reliable device for use in a wide variety of applications.

• ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DS}	Drain-Source Voltage	-100	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-Continuous	-23	A
I_{DM}	Drain Current-Single Pulsed	-76	A
P_D	Total Dissipation @ $T_c=25^\circ\text{C}$	140	W
T_j	Max. Operating Junction Temperature	175	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~175	$^\circ\text{C}$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(j-c)}$	Channel-to-case thermal resistance	1.1	$^\circ\text{C/W}$
$R_{th(j-a)}$	Channel-to-ambient thermal resistance	62	$^\circ\text{C/W}$



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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$; $I_D = -250\ \mu A$	-100			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$; $I_D = -250\ \mu A$	-2.0		-4.0	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS} = -10V$; $I_D = -11A$			0.1	Ω
I_{GSS}	Gate-Source Leakage Current	$V_{GS} = \pm 20V$			± 100	nA
I_{DSS}	Drain-Source Leakage Current	$V_{DS} = -100V$; $V_{GS} = 0V$			-25	μA
V_{SD}	Diode forward voltage	$I_S = -11A$; $V_{GS} = 0V$			-1.6	V